

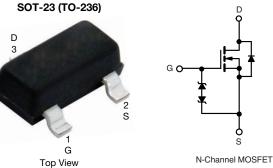
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Vishay Siliconix

# Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.085			
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 4.5 \text{ V}$	0.130			
I <sub>D</sub> (A)	4			
Configuration	Single			

# SOT-23 (TO-236)



Marking Code: 8Mxxx

#### **FEATURES**

- TrenchFET® Power MOSFET
- AEC-Q101 Qualified<sup>c</sup>
- 100 % Rq and UIS Tested
- Typical ESD Protection 800 V
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912





COMPLIANT HALOGEN FREE

ORDERING INFORMATION			
Package	SOT-23		
Lead (Pb)-free and Halogen-free	SQ2360EES-T1-GE3		

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	Drain-Source Voltage			V	
Gate-Source Voltage	$V_{GS}$	± 20	V		
Continuous Drain Current	T <sub>C</sub> = 25 °C	I <sub>D</sub>	4		
Continuous Drain Current	T <sub>C</sub> = 125 °C		2.3		
Continuous Source Current (Diode Conduction)	Continuous Source Current (Diode Conduction)			Α	
Pulsed Drain Current <sup>a</sup>	I <sub>DM</sub>	16			
Single Pulse Avalanche Current		I <sub>AS</sub>	6		
Single Pulse Avalanche Energy  L = 0.1 mH		E <sub>AS</sub>	1.8	mJ	
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	P <sub>D</sub>	3	W	
iviaximum Fower Dissipation "	T <sub>C</sub> = 125 °C		1	VV	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount b	R <sub>thJA</sub>	166	°C/W	
Junction-to-Foot (Drain)		$R_{thJF}$	50	C/VV	

#### Notes

- a. Pulse test; pulse width  $\leq 300 \, \mu s$ , duty cycle  $\leq 2 \, \%$ .
- b. When mounted on 1" square PCB (FR-4 material).
- c. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0$ , $I_D = 250 \mu A$		60	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		-	2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 5.5	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V	-	-	1	μΑ
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	-	-	50	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C	-	-	150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	V <sub>DS</sub> ≥ 5 V	10	-		Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 6 A, T <sub>J</sub> = 25 °C	=.	0.058	0.085	Ω
Drain-Source On-State Resistance a	Б	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 6 A, T <sub>J</sub> = 125 °C	=.	-	0.197	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 6 A, T <sub>J</sub> = 175 °C	-	-	0.258	0
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 5 A	=.	0.081	0.130	Ω
Forward Transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> =	-15 V, I <sub>D</sub> = 1.9 A	=.	5.8		S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			=.	295	370	pF
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	=.	55	70	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	35	55	
Total Gate Charge <sup>c</sup>	Qg			-	7.40	12	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 30 \text{ V}, I_{D} = 2 \text{ A}$	-	0.95	-	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			=.	1.94		
Gate Resistance	R <sub>g</sub>	f = 1 MHz		1.24	2.46	3.68	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	5	8	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 30 V, $R_L$ = 15 $\Omega$ $I_D \cong$ 2 A, $V_{GEN}$ = 10 V, $R_g$ = 1 $\Omega$		-	11	17	ns
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	10	15	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	8	12	
Source-Drain Diode Ratings and Chara	cteristics b						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	16	Α
Forward Voltage	$V_{SD}$	I <sub>F</sub> = 1.5 A, V <sub>GS</sub> = 0		-	0.8	1.2	V

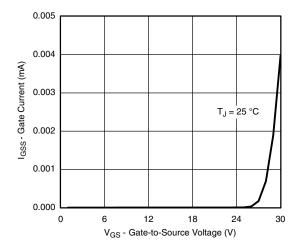
#### Notes

- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

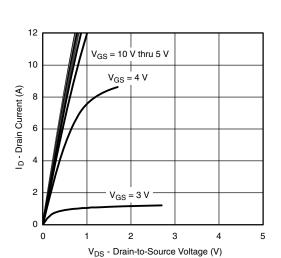
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



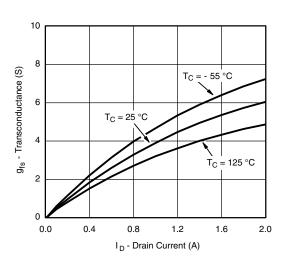
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



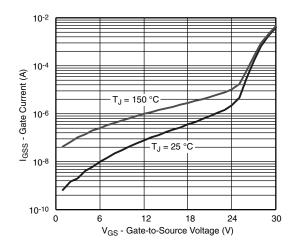
Gate Current vs. Gate-Source Voltage



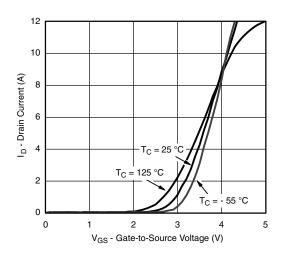
**Output Characteristics** 



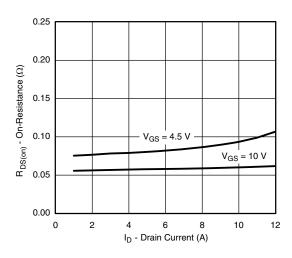
Transconductance



Gate Current vs. Gate-Source Voltage



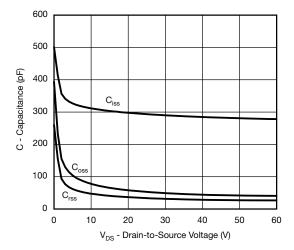
**Transfer Characteristics** 



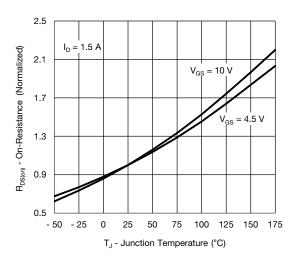
On-Resistance vs. Drain Current



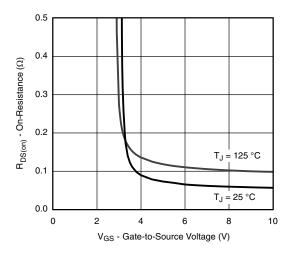
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



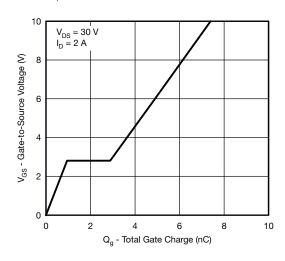
#### Capacitance



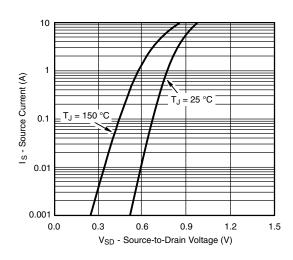
#### On-Resistance vs. Junction Temperature



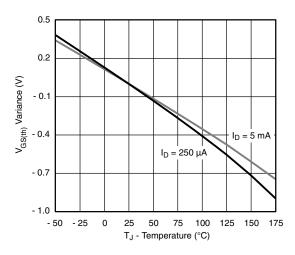
#### On-Resistance vs. Gate-Source Voltage



#### **Gate Charge**



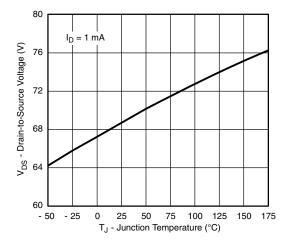
#### Source-Drain Diode Forward Voltage

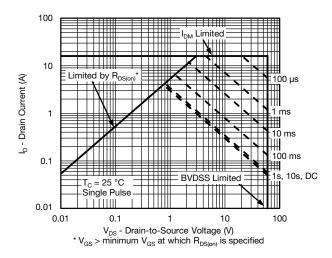


#### Threshold Voltage



## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

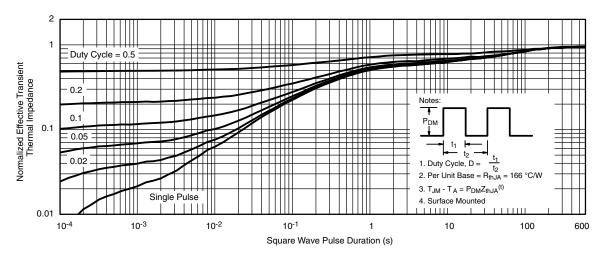




**Drain-Source Breakdown vs. Junction Temperature** 

Safe Operating Area

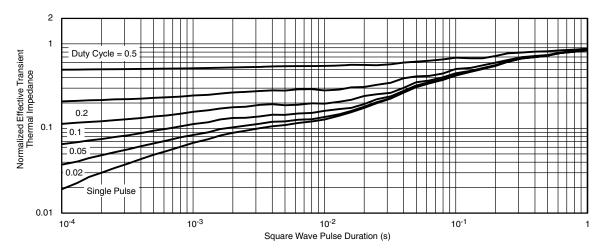
#### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65352.



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REVISION	REVISION HISTORY <sup>a</sup>				
REVISION	DATE	DESCRIPTION OF CHANGE			
F	04-Apr-14	<ul> <li>Correction of R<sub>DS(on)</sub> value used in calculation of maximum continuous drain current and safe operating area curve.</li> <li>V<sub>GS</sub> = 4.5 V curve added to on-resistance vs. junction temperature graph.</li> </ul>			

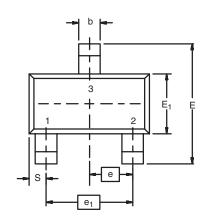
#### Note

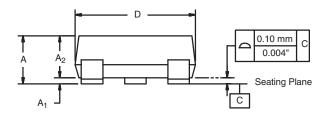
a. As of April 2014

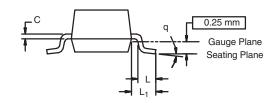


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# SOT-23 (TO-236): 3-LEAD







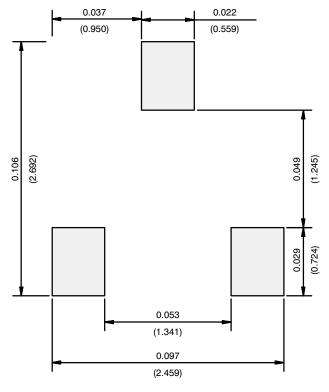
Dim -	MILLIN	IETERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A <sub>1</sub>	0.01	0.10	0.0004	0.004	
A <sub>2</sub>	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E <sub>1</sub>	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e <sub>1</sub>	1.90	1.90 BSC		8 Ref	
L	0.40	0.60	0.016	0.024	
L <sub>1</sub>	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
ECN: S-03946-Rev. K. 09-	Jul-01				

DWG: 5479

Document Number: 71196 www.vishay.com 09-Jul-01



#### **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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